Terahertz electroluminescence from Dirac-Landau polaritons

B. Benhamou-Bui¹, C. Consejo¹, S.S. Krishtopenko¹, S. Ruffenach¹, C. Bray¹, J. Torres¹, J.

Dzian², F. Le Mardelé², M. Orlita^{2,4}, A. Pagot³, X. Baudry³, P. Ballet³, S.V. Morozov^{5,6},

N.N. Mikhailov^{7,8}, S.A. Dvoretskii^{7,9}, B. Jouault¹, M. Orlita^{2,4}, C. Ciuti¹⁰, F. Teppe¹

¹ Laboratoire Charles Coulomb (L2C), UMR 5221 CNRS – Université de Montpellier, F-34095 Montpellier, France

² Laboratoire National des Champs Magnétiques Intenses,

CNRS - UGA - UPS - INSA - EMFL, Grenoble, France

³ CEA, LETI, MINATEC Campus, DOPT, Grenoble, France

⁴ Institute of Physics, Charles University, Prague, Czech Republic

⁵ Institute for Physics of Microstructures of the Russian Academy of Sciences, Nizhny Novgorod, Russia

Lobachevsky State University of Nizhny Novgorod, Nizhny Novgorod, Russia

A.V. Rzhanov Institute of Semiconductor Physics,

Siberian Branch of the Russian Academy of Sciences, Novosibirsk, Russia

Novosibirsk State University, Novosibirsk, Russia

Tomsk State University, Tomsk, Russia and

¹⁰ Université Paris Cité, CNRS, Matériaux et Phénomènes Quantiques, 75013 Paris, France

We report intense terahertz electroluminescence from Dirac-Landau polaritons, representing a major step toward achieving stimulated cyclotron emission and polariton-based lasers. By strongly coupling the cyclotron transitions of two-dimensional Dirac fermions in HgTe quantum wells with optical cavity modes, we observe efficient emission near the lasing threshold. This work demonstrates that polariton condensation–a process that bypasses the need for electronic population inversion–can significantly reduce the emission threshold compared to conventional mechanisms requiring high electric fields. Moreover, this concept unlocks the potential for stimulated emission in previously unsuitable narrow-gap semiconductors, as well as Dirac materials with non-equidistant Landau levels. These results open a new way for the development of compact, tunable terahertz lasers based on Landau polaritons, offering new opportunities for solid-state laser technology and applications in the terahertz gap.

I. INTRODUCTION

Bridging Terahertz (THz) technology gap [1] with a compact, powerful and tunable monochromatic solidstate source is a still unfinished objective of the THz community. Despite the development of quantum cascade lasers (QCLs) [2] and Schottky electronic emitters [3], a laser source tunable between 1 THz and 3 THz is still eagerly awaited. The use of cyclotron resonance (CR) in semiconductors is a very promising path to realize a THz laser that can be tuned by magnetic field [4]. As understood in the early 1960s [5–8], the key requirement for generating and amplifying electromagnetic radiation in the CR regime is the non-linear dynamics of charge carriers, achievable in semiconductors with strongly non-parabolic [6] or anisotropic [7, 8] band dispersions. Indeed, both types of energy bands result in non-equidistant Landau levels (LLs), which significantly suppresses Auger scattering and thereby minimizes nonradiative losses [9]. Experimental research on solid-state cyclotron or Landau lasers began in the 1970s, after understanding that inelastic scattering by optical phonons in strong electric field could induce a population inversion [10, 11]. Further theoretical investigations of scattering processes in both electric and magnetic fields revealed different possibilities for achieving an inverted distribution of charge carriers [12-14]. These studies laid the groundwork for the development of several Landau lasers based on bulk p-Ge, exploiting the nonparabolicity of the light-hole band [15–18] or the anisotropy of the heavy hole band [17]. The first type consists of lasers based on intraband LL transitions, either only between light holes [12, 18] or from light holes to heavy holes [17]. The latter type is represented by the Landau-based NEMAG [19] (Negative Effective Mass Amplifier and Generator), which covers a frequency range between 65 GHz and 375 GHz. Although the Landau emission has been intensively studied in various materials, such as n-type InSb [20], GaAs [21] and Si-inversion layers [22], the p-Ge lasers remain the only semiconductor Landau lasers ever successfully implemented to date.

The emergence of Dirac materials, with their band structure similar to that of relativistic particles, has renewed interest in Landau lasers, driven by the possibility to tune them across the THz technology gap using low magnetic fields. In this context, THz cyclotron emission from Dirac electrons has recently been observed in HgTe-based quantum wells (QWs). The distinctive band structure of these QWs, which results in non-equidistant LL spacing, effectively suppresses non-radiative Auger recombination [23]. This emission was found to be continuously tuneable across the THz gap, not only by the magnetic field but also by the carrier density. Following this pioneer work, it was established that this cyclotron emission can also be adjusted by a gate voltage at a fixed magnetic field, paying the way for an electrically controlled LL laser with a permanent magnet [24]. Unfortunately, reaching the lasing threshold in HgTe QWs requires the application of strong electric field, pushing the material dangerously close to its electrical breakdown. This makes it particularly difficult to achieve population inversion using conventional mechanisms which rely on electronic population inversion. To address this limitation, we propose an alternative approach: a new type of laser based on strong light-matter coupling. Specifically, we harness the stimulated scattering of bosonic Dirac-Landau polaritons—a mechanism that bypasses the need for electronic population inversion—thereby offering a promising path toward efficient and robust THz lasing in such systems.

The strong light-matter interaction occurs when the coupling between photons and a dipole active transition of the medium exceeds the losses in both components. This strong coupling regime gives rise to quasiparticles known as cavity polaritons, associated with a varietv of interesting physical phenomena[25] such as Bose-Einstein condensation, superfluidity, quantized vortices, and dark solitons. Another fascinating aspect of strong light-matter coupling is the phenomenon of polariton lasing, which arises from a polariton condensate. This phenomenon involves the occupation of a single-excitation state by a large number of polaritons, achieved with significantly lower input power compared to that required in conventional electronic lasers. This implies that the polariton lasers can achieve lasing operation without population inversion [26], with an emission threshold much lower than that of a conventional laser [27]. The typical polariton lasers, which can be optically [28-30] or electrically [31] pumped up to room temperature [32, 33], operate on the basis of the relaxation of exciton-polariton condensates [29, 30]. These hybrid particles are formed through the strong interaction between photons and excitons in microcavities. Despite the numerous other types of polariton couplings based on different light-matter interactions [34], only one other example of a polariton laser using a different hybrid particle has been developed, specifically an ultraviolet polariton laser based on plasmon-polaritons in ZnO-based Tamm cavities [35].

Several years ago, a new class of cavity polaritons resulting from the strong coupling of light to a Landau quantized 2D electron gas was theoretically predicted [36]. These quasiparticles, now known as Landau polaritons, were experimentally confirmed via reflectivity and transmission spectroscopy using split-ring resonators [37] and distributed Bragg reflectors [38] as cavities. These foundational experiments spurred extensive investigations into the distinctive properties [39–42] and promising applications of Landau polaritons. However, no study of spontaneous photon emission involving Landau polaritons has been reported to date. Here, we propose an original concept: the generation of Landau emission from a finely optimized electronic system of 2D Dirac fermions strongly coupled to photonic cavity modes. This novel approach demonstrates THz electroluminescence from Dirac-Landau polaritons, opening the door to the development of THz Landau polariton lasers. Through a thorough experimental exploration of cavity

length, carrier density, and electric and magnetic fields, we provide compelling evidence of strong light-matter interaction and THz light emission from Dirac-Landau polaritons.

II. RESULTS

A. Dirac-Landau polaritons

The optical excitations of a cavity-embedded 2DEG can be described by a Hopfield-like quantum Hamiltonian^[36] of the form H $H_{cavity} + H_{Landau} + H_{int} + H_{dia}$, where H_{cavity} is the bare Hamiltonian of the cavity, H_{Landau} describes the collective cyclotron excitation of the electrons occupying the Landau levels, H_{int} is the paramagnetic light-matter interaction, while H_{dia} is the diamagnetic contribution [36]. Note that this effective Hamiltonian contains only bosonic operators corresponding to the photon cavity and to the cyclotron excitation mode. The matter component of a Landau polariton is a collective cyclotron excitation: this was first demonstrated for GaAs/AlGaAs QWs, where the band structure is parabolic [37]. However, collective cyclotron excitations can occur also with non-parabolic band structures, as previously observed in Ref. 43, or even in Dirac systems exhibiting linear band dispersion. In this latter case, the energy of the inter-Landau level transitions no longer increases linearly with magnetic field B but instead follows a square root dependence on B. Additionally, the cyclotron mass is no longer constant but significantly depends on the Fermi energy. The quasi-particle associated with this strongly coupled light-matter system can be referred to as a Dirac-Landau polariton.

In order to study the cyclotron emission from these Dirac-Landau polaritons, it is necessary to first achieve the strong coupling regime between a resonant THz cavity and the CR of Dirac fermions. To achieve this, the measurement technique typically used in the literature for studying Landau polaritons is THz magnetoabsorption spectroscopy (see Figure 1). The selected system consists of a HgTe-based OW close to the gapless state (with a low-energy band structure represented by Dirac fermions), placed within an optical cavity designed for THz cyclotron frequencies [See Methods, Fig. 1 and 2]. To create the THz Fabry-Perot cavity with enhanced photon confinement and hence light-matter interaction, the substrate (GaAs for sample A and CdTe for sample B) of the QW was thinned. Before measuring the samples via magneto-reflectivity, we employed two distinct methods to characterize the formation of the optical cavity. The first method involved measuring multiple substrates with thicknesses ranging from 300 μ m to 40 μ m using THz Time Domain Spectroscopy (TDS). The second method involved directly measuring the same samples in emitter mode by detecting the thermal radiation emitted at zero magnetic field, while the sample was electrically heated. Both approaches confirmed the existence of a resonant optical cavity formed within the sample substrates (see Supplementary Materials – Fig. S.2,S.3 and S.4). The narrowest cavity was then analyzed using relative magneto-reflectivity measurements to characterize the coupling between the CR and the cavity modes. These results are compared to identical measurements taken in the absence of the THz cavity (see Fig. 1a and b).



FIG. 1. Magneto-reflectivity measurements on an 8 nm-thick HgTe QW (sample A) at T = 4.2 K. Top panel: sketch of the considered physical system, consisting of a 2D material with Dirac fermions embedded in a THz cavity resonator. A magnetic field is applied perpendicularly to the plane of the 2D material, creating quantized Landau electronic levels. The elementary optical excitations of the system are probed via reflection spectroscopy using an incident THz beam. Bottom panel: magneto-reflectivity spectra a) without a cavity and b) with a cavity resonator. The signal measured in the QW without a cavity, shown as a color plot, exhibits a linear evolution of cyclotron energy as a function of the applied magnetic field. In the presence of a 28 μ m-thick cavity, the CR signal is significantly modified, displaying spectral anti-crossings at magnetic fields of 0.7 T and 2 T, corresponding to energies of 3 meV and 10 meV, respectively.

The magneto-reflectivity results obtained without the cavity clearly reveal a CR whose energy evolves linearly with the applied magnetic field. The system is not in a semi-classical regime but already in the Shubnikov-de Haas or incipient Landau quantization regime, where LLs are present but partially overlap (see Supplementary Materials – Equation S.4). Even though the CR energy evolves linearly with the magnetic field, the slope of the CR changes with the concentration of electrons. The cyclotron mass extracted from a linear fit is $m_{cyc} = 0.024m_0$, which is consistent with the carrier density

measured in this sample (See Supplementary Materials – Figure S.4).

In the presence of the cavity, the CR energy dispersion is significantly modified due to the interaction with two cavity modes with respective energies $\hbar\omega_1 = 3$ meV and $\hbar\omega_2 = 10$ meV. These interactions result in pronounced energy anti-crossings, giving rise to two distinct pairs of Landau upper and lower polariton branches: (UP1, LP1) around 0.7 T and (UP2, LP2) around 2 T. Fitting these results using the Hopfield polariton model (see Supplementary Materials, Equation S.8 and Figure S.6) yields excellent agreement, with coupling strengths of $\hbar\Omega_1 = 0.65$ meV and $\hbar\Omega_2 = 0.6$ meV.

B. Electroluminescence

To study now the cyclotron emission from Dirac electrons in HgTe QWs with relativistic band dispersion under a quantizing magnetic field, short electric pulses are applied on the sample to populate high-energy empty LLs with non-equilibrium Dirac electrons. Due to the non-equidistant spacing of these relativistic LLs, nonradiative Auger recombination is suppressed [23]. At magnetic fields on the order of a few hundred of mT, cyclotron emission occurs, and a characteristic Gaussianshaped spectrum is measured. In the absence of a cavity, the electroluminescence peak shifts linearly with the magnetic field (see Fig. 2 a). The position of the peak plotted as a function of the magnetic field in Fig. 2 a) exhibits a slope that is in good agreement with the cyclotron resonance observed in the magneto-reflectivity measurements (Fig. 1 a). However, in the presence of the cavity, the electroluminescence spectrum is drastically modified (Fig. 2 b and c).

The emission is not observed below the energy of the first cavity mode and no longer exhibits a linear dependence on the magnetic field. Instead, the emission spectrum reveals multiple peaks, with their positions remaining constant in the low magnetic field limit. As detailed in the Supplementary Information (Fig. SM2), this behavior is observed in several samples with different cavity widths and materials. The sample with the widest cavity (50 μ m) exhibits three cavity modes (Fig. 2 b), whereas only two modes appear in the emission spectra of the thinnest (28 μ m) cavity (Fig. 2 c). At stronger magnetic fields, however, and especially in the thinnest cavity, the peaks shift significantly towards higher energies, eventually approaching the emergence of the higher energy peak. When plotted as a function of the magnetic field in Fig. 2d, the peak positions obtained from the thinnest cavity sample clearly exhibit two distinct inflections in the cavity modes, indicating anticrossings at the energies of 4 and 10 meV, identified to be UP1 and UP2 thanks to the reflectivity measurements. By applying the Hopfield polariton model with the same fitting parameters used for the magneto-reflectivity results, we achieve excellent agreement between the electroluminescence and



FIG. 2. Cyclotron electroluminescence from an 8 nm-thick HgTe QW (sample A) at T = 4.2 K:. Top panel: sketch of the considered THz electroluminescent cavity device, where an in-plane electrical bias injects current through source and drain ohmic contacts. Bottom panel: THz emission spectra a) without a cavity and b, c, d) with a resonant cavity. Electroluminescence spectra at different magnetic field values: a) without a cavity on a 300 μ m-thick substrate; b, c) with a cavity on 50 μ m and 28 μ m-thick substrates, respectively. Red dashed lines serve as visual guides. a) The energy scales linearly with the magnetic field, characteristic of cyclotron emission from Dirac electrons in the incipient Landau quantization regime. b) The 50 μ m cavity reveals three cavity modes at 4, 7, and 10 meV, which couple to the CR. c) The thinner 28 μ m cavity exhibits only two cavity modes at 4 and 10 meV, with stronger anticrossings due to enhanced light-matter coupling. d) The emission peak energy in the 28 μ m cavity, plotted as a function of the magnetic field, aligns well with magneto-reflectivity UP1 and UP2 features.

reflectivity data for such polariton energy dispersion.

Remarkably, the linewidth of the cyclotron emission consistently exceeds that of the absorption. This broadening arises because spontaneous cyclotron emission involves hot electrons that cover a broader energy range compared to the quasi-equilibrium absorption process. Specifically, the emission line shape is influenced by the non-equilibrium electron distribution induced by the electric field [44], as well as inhomogeneous broadening from electron-phonon scattering [45] and Stark broadening due to ionized impurities [46, 47]. Nevertheless, the emission energy maxima align well with the expected dispersion of the upper polariton branch, as observed in magnetoreflectivity, confirming the electroluminescence of Landau polaritons (see Fig. S.7 for a clear mirroring of emission and reflectivity spectra).

Notably, the lower polariton branch is never observed in the emission mode. This behavior may result from a bottleneck effect, significantly affecting the redistribution of polaritons between the upper and lower branches [48–50]. This phenomenon arises from a complex interplay of energy relaxation mechanisms, including polariton-phonon coupling, polariton-carrier, and polariton-polariton scattering, as well as intrinsic system losses. While exciton-polaritons in the near-infrared

typically relax efficiently toward the lower branch [29], our Landau system exhibits the opposite trend, with electroluminescence dominated by the upper branch. A possible explanation lies in the combined effects of nonequidistant Landau levels and the non-equilibrium carrier dynamics induced by electrical excitation, particularly for carriers occupying states well above the Fermi energy. These electrons can absorb energy at lower scales due to the reduced spacing between Landau level. Furthermore, this effect may be amplified by crossed electric and magnetic fields, where higher energy levels shift downward more rapidly than lower ones [51]. Coulomb interactions could further enhance this process by converting polaritons into electron-hole excitations at the same energy via interactions with these non-equilibrium carriers. To fully elucidate and harness these effects, future experimental and theoretical studies will be essential. These investigations should focus on understanding the relaxation dynamics from hot carriers to polariton excitations, refining models of Landau levels in crossed-field configurations, and exploring the distribution of non-equilibrium carriers within the Landau levels.

The Dirac-Landau polaritons exhibit distinctive features with respect to the standard Landau polaritons. Since the effective mass of Dirac electrons depends on



FIG. 3. Influence of the gate voltage on coupling strength and critical magnetic field. Due to the relativistic nature of charge carriers, their concentration in the QW determines the cyclotron mass and thus the slope of the Landau emission. By tuning the carrier density from $n_s = 1.83 \times 10^{11} \text{ cm}^{-2}$ to $2.98 \times 10^{11} \text{ cm}^{-2}$, the cyclotron mass increases, shifting the critical magnetic field for the anticrossing from approximately 0.7 T to 0.9 T. (Main) Extracted emission maxima from spectra measured at different magnetic field values for sample B, with a gate bias of -100 V(purple empty circles) and +100 V (blue empty circles). The dashed lines represent fits based on the model developed in Ref.37. (Inset) Evolution of the reduced coupling strength as a function of electron density (black line), based on the model in Ref.37 and the low-energy model describing the cyclotron mass dependence on density [24]. The violet (resp. blue) star represents the extracted reduced coupling strength from the emission curve for a gate bias of -100 V (resp. +100 V). The model has been rescaled to match the experimental values.

the electron density [23], the cyclotron mass and, consequently, the CR slope are continuously tunable via the back-gate voltage [24]. Therefore, the critical magnetic field at which the anticrossing occurs can also be tuned by adjusting the gate voltage (see Figs. 3 a,b,c). Even more interestingly, since the coupling strength term depends on the cyclotron mass, it can be tuned as well with the gate voltage, as illustrated in Figs. 3 b, c). According to the Hopfield polariton model, where the cyclotron mass is derived from the Bernevig-Hughes-Zhang (BHZ) model [23], the coupling strength can reach 30% in this non-optimized system, for a realistic carrier density of 1 $\times 10^{12}$ cm⁻².

III. DISCUSSION

Previously, the conditions required for achieving the streaming effect and potential population inversion of Landau levels in HgTe QWs without a cavity were estimated [23] by comparing the momentum relaxation time, derived from carrier mobility, with the time-offlight needed for an electron to reach the longitudinal optical (LO) phonon energy (18.3 meV for HgTe QWs [52]). It was established that population inversion requires electric fields on the order of 6 kV/cm at 1 T, approximately 10 to 100 times higher than those typically used in our measurements. In contrast, we focus on polariton condensation, where a large number of polaritons coalesce into a single quantum state at densities significantly lower than those required for population inversion in conventional lasers. Polariton lasers operate through stimulated polariton scattering, benefiting from final-state occupation effects, and exhibit an emission threshold far lower than that of traditional lasers. This discussion explores the conditions under which such amplification effects can be realized for Landau polaritons in HgTe QWs.

The amplification phenomenon in polariton systems is expected to occur when the average number of polaritons per mode reaches one. To evaluate the number of polaritons per mode under our experimental conditions, it is first necessary to determine the relevant number of modes. This is achieved by calculating the product of the density of states and the energy corresponding to the emission linewidth (see Supplementary Materials). For our setup, the number of modes is approximately 1500. A lower and upper bound for the polariton population in the mode with the highest emission can then be established.

The lower bound assumes a uniform distribution of excitations among all modes. Using this assumption and the emitted power (estimated at 10 nW, as detailed in the Supplementary Materials), the total number of polaritons is approximately 30. Consequently, the number of polaritons per mode at an electric field of 300 V/cmis on the order of 2×10^{-2} . Conversely, the upper bound for the polariton occupation number assumes that all polaritons are concentrated in a single mode. Under this assumption, as detailed in the Supplementary Materials, the number of polaritons per mode ranges from 0.3 to 1.3 at 1 kV/cm, depending on the cavity mode (see insert of Fig. 4b). This upper bound suggests that the system is close to the lasing threshold at 1 kV/cm. However, as we demonstrate below, the system remains in an intermediate regime between the lower and upper bounds.

To investigate this further, we analyzed the influence of the applied electric field, and consequently the injected electrical power, on the cyclotron emission power (see Fig. 4a). The emitted optical power exhibits a superlinear increase with the injected electrical power across the applied electric field range of 300 to 1000 V/cm (see Fig. 4b), suggesting that while lasing has not yet been achieved under these conditions, the system is approaching the threshold.

Another approach to estimating the polariton population is to study the evolution of the emission peak spectral linewidth (full width at half maximum) as the electrical injection bias increases. Fig. 4c shows that the UP2 emission peak spectrally narrows while increasing the electrical power P and reaches a minimum around 0.5



FIG. 4. Influence of the electric field on cyclotron emission. (a) Electroluminescence spectra measured at a fixed magnetic field of 0.9 T on sample A for different peak-to-peak injection biases ranging from 60 to 200 V. (b) Evolution of the two emission peaks, corresponding to the UP1 and UP2 polariton modes, as a function of the injected electrical power. The marker style and color indicate the corresponding electroluminescence peaks in (a). The optical power was obtained by multiplying the peak amplitude by the sensitivity of the InSb detector. The electrical power was estimated as P = VI, where V is the applied bias and I is the current through the sample. Dashed lines depict the evolution of the polariton population, based on the non-linear dependence of the emitted power on the injected electrical power (see Supplementary Materials). (c) Evolution of the full-width at half maximum (γ) of the UP2 peak (magenta markers) as a function of the injected electrical power P. The dashed line is a fit using the formula described in text in Eq. 1, accounting for Schawlow–Townes polariton narrowing and power-induced broadening at the lowest order in P.

W. Increasing further P the linewidth increases and for power exceeding 0.8 W, there is net broadening with respect to the low-power regime. This could be attributed to non-linear polariton losses caused by scattering processes [53], where a polariton is converted into an excitation of carriers in higher-energy Landau levels, as discussed earlier in the text. We can model in a general way the power-dependent emission linewidth with the formula

$$\gamma(P) = \frac{\gamma(0)}{1 + N_{pol}(P)} + \gamma_{NL}(P), \qquad (1)$$

where $N_{pol}(P)$ is the polariton occupation number and $\gamma_{NL}(P)$ is a power-induced additional broadening. This formula includes both Schawlow–Townes narrowing produced by stimulated scattering due to the polariton finalstate population and nonlinear losses. At the lowest order in the power, $N_{pol}(P) \simeq \mathcal{N}P$ and $\gamma_{NL}(P) \simeq \eta P$, since both quantities vanish for $P \to 0$. With this formula we achieve an excellent fit of the experimental linewidth versus power, as shown in Fig. 4c with the fitting parameters $\gamma(0) = 5.65 \text{ meV}$, $\mathcal{N} = 2.0 \text{ W}^{-1}$ and $\eta = 3.1 \text{ meV/W}$. For a power P = 0.5 W, the estimated polariton occupation number is 1, which is consistent with the previous discussed bounds.

Lasing with Dirac-Landau polaritons offers significant advantages. Indeed, the polariton lasing threshold is critically influenced by the loss rate of the polariton modes, which can be optimized by improving both the cavity quality factor and the cyclotron loss rate. Currently, the quality factor of the resonant cavity in our samples is only about $Q \approx 4$ (from the reflectivity spectra). Optimized structures incorporating THz distributed Bragg mirrors around the QW, configured as a Tamm cavity [54], could significantly improve performance. Notably, recent THz Tamm cavities have demonstrated quality factors of Q = 37 at 1.5 THz [55], while Landau polariton structures with distributed Bragg reflectors have achieved values exceeding 500 [38]. The enhancements should promisingly lower the stimulation threshold to allow lasing well before the onset of nonlinear losses.

The use of Landau polaritons unlocks exciting opportunities for exploring stimulated cyclotron emission in solids. Beyond HgTe QWs, this approach enables the consideration of materials previously deemed unsuitable for stimulated emission via the streaming effect due to the requirement for prohibitively high electric fields. By leveraging strong light-matter coupling, these materials can become viable candidates for stimulated emission. As a result, materials where spontaneous cyclotron emission has been observed but stimulated emission was unattainable. Similarly, the challenges associated with the p-Ge cyclotron laser, where electrical excitation approaches the material's breakdown threshold, could be mitigated by reducing the required electric field amplitude through the polariton condensation effect. More broadly, a wide range of Dirac materials with non-equidistant Landau levels can now be realistically explored for such applications, further expanding the landscape of cyclotron-based light sources and lasers. Notably, spontaneous CR emission in the mid-infrared range was recently demonstrated in electrically biased monolayer graphene [56], underscoring the potential of these mechanisms for future THz and infrared light sources.

IV. CONCLUSION

In conclusion, our study demonstrates THz electroluminescence from Dirac-Landau polaritons, marking a significant step toward stimulated cyclotron emission and polariton-based lasers. Conventional solid-state lasers face challenges due to the high electric fields required for population inversion, but polariton effects offer a promising alternative by lowering the emission threshold. Although the current cavity quality factors remain limited, future advancements—such as THz Tamm structures, Bragg reflectors, or multi-quantum well designs—could further reduce the lasing threshold. Beyond HgTe QWs, this approach could be extended to other materials previously deemed unsuitable for stimulated emission due to their high breakdown voltages. These results pave the way for the development of THz cyclotron lasers, broadening the scope of materials and applications in this domain.

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AUTHOR CONTRIBUTIONS STATEMENT

The experiment was proposed by FT. The samples were fabricated by XB, PB, NNM and SAD. THz cyclotron emission experiments were carried out by BBB and CCo. The magnetoreflectivity experiments were carried out by BBB, FLM, JD and MO. Interpretation of the results was done by CCi, BBB and FT, and all co-authors discussed the experimental data and interpretation of the results. Characterization measurements were conducted and/or analysed by SR, CB, BJ and SSK. BBB, CCo handled the data and prepared the figures. BBB, CCi and FT wrote the manuscript and all the coauthors corrected it.

COMPETING INTERESTS STATEMENT

The authors declare no competing financial interests.

METHODS

Samples

Two types of samples were studied, both grown via Molecular Beam Epitaxy (MBE) on GaAs-(013) or CdTe-(100) substrates (see Table I for details). Two distinct buffer layers were employed, as illustrated in Figure S.1. The active layer consists of a HgTe QW with HgCdTe barriers, with only one sample type incorporating a CdTe cap layer. To create an optical cavity, the substrates were thinned below 50 μ m using two techniques: (i) micrometric rotary sawing down to 40 μ m or (ii) mechanical polishing to 50 μ m, followed by inductively coupled plasma etching to further reduce the thickness below 30 μ m. The samples were then mounted on a gold sample holder.

Landau emission measurement technique

Higher Landau levels are populated using short electrical pulses with a frequency of 127 Hz, peak-to-peak amplitudes ranging from 40 V to 200 V, and durations between 1 ms and 30 μ s. These pulses are applied to the sample via indium balls soldered onto its surface, which diffuse into the structure, forming high-quality ohmic contacts. The experimental setup includes a Landau spectrometer with three superconducting coils housed in a liquid helium cryostat (see [23] for details). The detector is an *n*-type InSb bolometer, which operates under a strong magnetic field to refine and narrow its detection energy window. The second coil resolves the LL structure of the sample, while the third coil decouples the contributions of the first two fields.

The measurement protocol involves fixing the sample's magnetic field while sweeping the detector's magnetic field, enabling energy spectra acquisition at a constant sample field. The detector signal is amplified by a low-noise amplifier and processed via a boxcar averager, ensuring a high signal-to-noise ratio even for low-duty-cycle pulses ranging from 0.4% to 1%. All measurements were performed at 4.2 K.

Sample name	Substrate	Thickness	Cavity mode energies	Carriers density $[cm^{-2}]$
091222 (sample A)	GaAs	$28~\mu{\rm m}$	$3.1~{\rm meV}$; $10~{\rm meV}$	$7 \ge 10^{11}$
28104 (sample B)	CdTe	$40~\mu{\rm m}$	$5~{\rm meV}$; $9~{\rm meV}$	$3 \ge 10^{11}$

TABLE I. Table summarizing the different samples' characteristics.

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SUPPLEMENTARY MATERIAL

Supplementary Material for the article: "Terahertz electroluminescence from Dirac-Landau polaritons"

B. Benhamou-Bui¹, C. Consejo¹, S.S. Krishtopenko¹, S. Ruffenach¹, C. Bray¹, J. Torres¹, J.

Dzian², F. Le Mardelé², M. Orlita^{2,4}, A. Pagot³, X. Baudry³, P. Ballet³, S.V. Morozov^{5,6},

N.N. Mikhailov^{7,8}, S.A. Dvoretskii^{7,9}, B. Jouault¹, M. Orlita^{2,4}, C. Ciuti¹⁰, F. Teppe¹

¹ Laboratoire Charles Coulomb (L2C), UMR 5221 CNRS – Université de Montpellier, F-34095 Montpellier, France

² Laboratoire National des Champs Magnétiques Intenses,

CNRS - UGA - UPS - INSA - EMFL, Grenoble, France

³ CEA, LETI, MINATEC Campus, DOPT, Grenoble, France

⁴ Institute of Physics, Charles University, Prague, Czech Republic

⁵ Institute for Physics of Microstructures of the Russian Academy of Sciences, Nizhny Novgorod, Russia

⁶ Lobachevsky State University of Nizhny Novgorod, Nizhny Novgorod, Russia

A.V. Rzhanov Institute of Semiconductor Physics,

Siberian Branch of the Russian Academy of Sciences, Novosibirsk, Russia

Novosibirsk State University, Novosibirsk, Russia

⁹ Tomsk State University, Tomsk, Russia and

¹⁰ Université Paris Cité, CNRS, Matériaux et Phénomènes Quantiques, 75013 Paris, France

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Cavity characterization



FIG. S.1. Schematic representation of the sample layer structure. The core consists of a HgTe quantum well (QW) sandwiched between HgCdTe barriers with a Cd composition of 68%. A CdTe/ZnTe buffer layer is inserted beneath the QW to facilitate strain relaxation before reaching the substrate.

When the substrate is thin, i.e. on the order of $\lambda/2$ for the cyclotron wavelength, the emission spectrum is strongly modified by the presence of cavity electromagnetic modes. The metal contact placed on the back side of the sample and the helium/semiconductor interface on the front side act as mirrors for a vertical resonant THz cavity. In order to characterize the cavity effect, we performed emission measurements at zero magnetic field. When the LLs are not yet established, the emis-



FIG. S.2. Emission spectra obtained at 4.2 K, at zero magnetic field, on sample A, for different substrate thicknesses. On the bare sample (300 μ m), the spectrum exhibits no structuration. When the substrate thickness is reduced below 100 μ m, additional extrema (blue dashed lines) emerge, indicating a cavity effect. Notably, the 8 meV line in the 80 μ m sample and the 9.5 meV line in the 64 μ m sample (grey dashed lines) are barely visible at B = 0 T but become observable through cyclotron resonance at finite magnetic fields.

sion spectrum is not related with the CR and is primarily

composed of blackbody radiation, most likely originating from the heating of the current injection contacts. When the dimensions of a thermally emitting object are on the order of the thermal radiation wavelength λ_{Th} , its emission can indeed substantially differ from the predictions made by Planck's law [57, 58], creating new possibilities in the realm of thermal radiation. For instance, the presence of some Fabry-Pérot cavity modes can greatly enhance thermal emission, producing a narrow-band emission spectrum consistent with the Purcell effect. Moreover, the spectral emission power can exceed the limits imposed by Planck's law for blackbody radiation [59].

Figure S.2 below shows these emission spectra plotted for the different sample thicknesses. When the substrate is thick, the blackbody emission spectrum is broadband, and its peak is, as expected, red shifted as the injection current decreases. When the substrate is reduced to thicknesses comparable to the wavelength of thermal radiation defined by Wien's displacement law, the broadband blackbody radiation transforms, uncovering peaks at energies aligned with the substrate's optical cavity modes. The interaction between the resonant modes of the cavity induces a narrower thermal emission bandwidth [60, 61]. Indeed, since the sample acts at zero magnetic field as both a thermal heat source and an optical cavity, its thermal radiation is modulated by the cavity modes according to the Purcell effect.

The emission signal is structured into a series of peaks, with their positions varying depending on the substrate thickness. We then compare in Figure S.3 these energy positions with a simulation using the Transfer Matrix Method (TMM) [55]. Taking into account the sample geometry (thinned substrate on a gold sample holder) and the complex refractive index of the material, we were able to accurately reconstruct the energy positions of the modes for the different thicknesses. There is excellent agreement between the experimental data and the simulation, as the theoretical thicknesses used to reproduce the results closely match those measured experimentally.



FIG. S.3. Evolution of cavity mode energies extracted from Fig. SM2 for three different samples with varying substrate thicknesses (empty circles). Triangular markers correspond to data obtained at high magnetic fields. The energy values were deduced from the B = 0 T emission spectra. A Transfer Matrix Method (TMM) prediction (dashed lines) is overlaid, showing excellent agreement with the experimental data.

Another way to characterize the cavity effect in-

duced by the substrate is to perform room temperature THz reflectivity thanks to a commercial Time-Domain-Spectroscopy (TDS) setup. Figure S.4 below shows two spectra obtained on the two thinnest samples. It clearly displays some reflectivity minima, well corresponding to the cavity modes. These minima positions, when extracted, are once again in a very good agreement with the TMM simulations.



FIG. S.4. **THz reflectivity and transmission analysis.** (Left panel) TDS reflectivity spectra measured for samples A and B. (Right panel) Transmission minima extracted and plotted against an arbitrary index (empty circles). A TMM-based prediction (dashed lines) is overlaid, showing excellent agreement with the experimental data.

Magneto-transport measurements – Shubnikov-de Haas regime

The electron densities of the samples are determined using the standard Shubnikov-de Haas magnetotransport technique. Figure S.5 below presents the typical magneto-resistance behavior of our samples. The observed oscillations enable us to extract the electron density via the well-known formula:

$$n_S = \frac{e}{h \cdot \Delta(1/B)}, \qquad (S.1)$$

where $\Delta(1/B)$ is the inverse magnetic field period of the oscillations. For the sample shown below, this yields $n_S = 7.0 \times 10^{11} \text{ cm}^{-2}$.

Additionally, cyclotron resonance measurements allow us to determine the cyclotron mass of the sample (see main text). By combining these results, we can verify the predicted evolution of the cyclotron mass as a function of electron density, as derived from the low-energy model[23]. The inset demonstrates excellent agreement between the experimental data and the theoretical model.

Regarding the magneto-reflectivity and cyclotron emission results, it is important to note that the system operates within the Shubnikov-de Haas regime. This implies that the Landau levels (LLs) are already present but still exhibit partial overlap. These conditions, which lie between the classical and quantum regimes, are often referred to as the incipient Landau quantization regime.



FIG. S.5. Longitudinal magneto-resistance and cyclotron mass evolution. Shubnikov-de Haas oscillations measured in the longitudinal magneto-resistance of sample A. (Inset) Theoretical dependence of the cyclotron mass on electron density, based on a low-energy model [23]. The red star represents the experimental value extracted from reflectivity and magneto-transport measurements, showing consistency with theoretical predictions.

Similar to the classical case, the cyclotron resonance (CR) energy evolves linearly with the applied magnetic field. This occurs because, as the magnetic field increases, the Fermi level oscillates between adjacent LLs. Consequently, even though the LLs in the system are relativistic and follow a \sqrt{B} dependence, the energy of optical transitions between these levels remains linear in the magnetic field. This can be understood by considering the energy difference between two adjacent LLs, n+1

and n:

$$\hbar\omega_c = \sqrt{2v_F^2 eB \hbar} \left(\sqrt{n+1} - \sqrt{n}\right) \text{ with } E_F = \sqrt{2v_F^2 eB \hbar} \sqrt{n}$$
(S.2)
(S.2)

$$\sqrt{n+1} - \sqrt{n} \simeq \frac{1}{2\sqrt{n}}, \qquad (S.3)$$

we finally have

$$\begin{split} \hbar\omega_c &= \sqrt{2v_F^2 eB\hbar} \left(\sqrt{n+1} - \sqrt{n}\right) \\ &\simeq \sqrt{2v_F^2 eB\hbar} \frac{1}{2\sqrt{n}} \\ &= \frac{2v_F^2 eB\hbar}{2E_F} = \frac{eB\hbar}{m_c}, \end{split} \tag{S.4}$$

where we defined $m_c = \frac{E_F}{v_E^2}$.

Landau polariton: Fitting procedure

To extract the coupling strength from the reflectivity measurements, we followed the same procedure as in [37]. It is based on the following total Hopfield Hamiltonian [36]:

$$H = H_{cavity} + H_{Landau} + H_{int} + H_{dia}, \qquad (S.5)$$

where H_{cavity} is the bare Hamiltonian of the cavity, H_{Landau} describes the collective cyclotron excitation of the electrons occupying the Landau levels, H_{int} is the paramagnetic light-matter interaction, while H_{dia} is the diamagnetic contribution. The polariton excitations can be obtained by diagonalizing the following Hopfield-Bogoliubov matrix:

$$M_{j}(B,\chi_{j}) = \hbar \begin{pmatrix} \omega_{c} & \chi_{j}\sqrt{\omega_{c}} & 0 & \chi_{j}\sqrt{\omega_{c}} \\ \chi_{j}\sqrt{\omega_{c}} & \omega_{j} + 2\chi_{j}^{2} & \chi_{j}\sqrt{\omega_{c}} & 2\chi_{j}^{2} \\ 0 & -\chi_{j}\sqrt{\omega_{c}} & -\omega_{c} & -\chi_{j}\sqrt{\omega_{c}} \\ -\chi_{j}\sqrt{\omega_{c}} & -2\chi_{j}^{2} & -\chi_{j}\sqrt{\omega_{c}} & -\omega_{j} - 2\chi_{j}^{2} \end{pmatrix},$$
(S.6)

where

$$\chi_j = \frac{\Omega_j}{\sqrt{\omega_c}} \tag{S.7}$$

is a fitting parameter, independent of the magnetic field, Ω_i being the collective polariton coupling (Rabi) frequency for the electromagnetic mode j. By diagonalizing this Hamiltonian, we can access the theoretical polaritonic branches, labelled $\omega_i^{UP}(B,\chi)$ (resp. $\omega_i^{LP}(B,\chi)$) for the upper branch (resp. lower branch). Therefore, we can extract the coupling strength by minimizing the quantity

$$RMSD_{j}(\chi) = \sqrt{\frac{\sum_{\chi}^{N_{exp}} \left[\left(\omega_{j,\eta}^{UP} - \omega_{j}^{UP}(B_{\eta},\chi) \right)^{2} + \left(\omega_{j,\eta}^{LP} - \omega_{j}^{LP}(B_{\eta},\chi) \right)^{2} \right]}{2N_{exp}}},$$
(S.8)

where N_{exp} is the number of experimentally measured

points. One example of minimization is shown in Fig.



FIG. S.6. Normalized root-mean-square deviation analysis for sample A. Evolution of the normalized rootmean-square deviation for the two electromagnetic modes. The minima correspond to normalized coupling strengths of 21% and 4% for the lower and higher modes, respectively, indicating distinct interaction regimes.

Estimation of the number of polaritons per mode

Lower bound estimate

Let us consider the cavity energy dispersion

$$E_{cav}(k) = \frac{\hbar c}{n} \sqrt{k_z^2 + k^2}, \qquad (S.9)$$

where c is the speed of light, n the refractive index of the substrate, z is the direction perpendicular to the 2D material. For small in-plane wave vectors, the cavity dispersion can be approximated as parabolic, namely:

$$E_{cav}(k) = \frac{\hbar c}{n} k_z \sqrt{1 + \frac{k^2}{k_z^2}} \simeq E_{cav}(0) \left(1 + \frac{1}{2} \frac{k^2}{k_z^2}\right).$$
(S.10)

The density of photonic states is

$$\mathcal{D}(E) \simeq \frac{A}{(2\pi)^2} \int d^2k \,\delta(E - E_{cav}(k))$$
$$= \frac{A}{2\pi} \int k dk \,\delta(E - E_{cav}(k)), \qquad (S.11)$$

where A is the area of sample where there is emission. Since $dE_{cav} = E_{cav}(0)\frac{kdk}{k_z^2}$, then $kdk = \frac{k_z^2}{E_{cav}(0)}dE_{cav}$ and therefore

$$\mathcal{D}(E) \simeq \frac{A}{2\pi} \frac{k_z^2}{E_{cav}(0)} \,. \tag{S.12}$$

The polariton density of states is comparable to the photonic density of states, which will be used for our estimate of the number of polariton modes involved in the emission process:

$$\mathcal{N}_{mode} \simeq \mathcal{D}(E) \,\Delta E_{emission} = \frac{A}{2\pi} k_z^2 \frac{\Delta E_{emission}}{E_{cav}(0)} \,, \,\,(\text{S.13})$$

where ΔE_{em} is the emission linewidth. Given the experimental nominal parameters, we can take $A \simeq 1 mm^2$, $k_z = \frac{\pi}{L_{cav}} = \frac{\pi}{30\mu m} = 10^5 m^{-1}$ and $\Delta E_{emission} = 3 \text{ meV}$ we have $E_{cav}(0) \simeq 3 \text{ meV}$ we get $\mathcal{N}_{mode} \simeq 1500$. Finally, we can estimate the number of polariton via the emitted power:

$$\mathcal{P}^{emission} \simeq N_{pol} \, \gamma^{avg}_{rad} \, \hbar \omega^{avg}_{pola} \,, \qquad (S.14)$$

where N_{pol} is the number of polaritons in the steady state, γ_{rad}^{avg} the average radiative rate and $\hbar \omega_{pola}^{avg}$ the average photon emission energy. By injecting the experimental values $\mathcal{P}^{emission} \simeq 10nW$, $\hbar \omega_{pola}^{avg} \simeq 3 \text{ meV}$ and $\gamma_{rad}^{avg} \simeq \frac{\Delta E_{emission}}{h} = \frac{3 \text{ meV}}{h} \simeq 0.7 \text{ ps}^{-1}$ we get: $N_{pol} \simeq 30$. Finally, we get the lower bound:

$$\frac{N_{pol}}{\mathcal{N}_{mode}} > 2 \cdot 10^{-2} \,. \tag{S.15}$$

Upper bound estimate

The upper bound for the polariton occupation number is obtained by assuming that all the polaritons are occupying the same polariton mode. This is certainly not the case, but together with the lower bound calculated above will allow us to have a decent estimate of the polariton occupation numbers. Assuming that only one mode participates to the emission, we can estimate the polariton population from the non-linear dependence of the emission amplitude with respect to the injected electrical power. This can be calculated via the simple rate equation:

$$\frac{dN_{pol}}{dt} \simeq -\gamma N_{pol} + \eta V_{pp} (1 + N_{pol}) , \qquad (S.16)$$

where γ is the polariton loss rate and η is unknown. The steady-state solution reads:

$$N_{pol} = \frac{\eta V_{pp}}{\gamma - \eta V_{pp}} \,. \tag{S.17}$$

From this equation we can see that for $P_{elec} \rightarrow P_{elec}^{(thresholds)} = \frac{\gamma}{\eta}$ then $N_{pol} \rightarrow +\infty$. Below threshold, we can Taylor-expand the previous solution as follows:

$$N_{pol} = \frac{\eta P_{elec}}{\gamma} \frac{1}{1 - \frac{\eta P_{elec}}{\gamma}} \simeq \frac{\eta P_{elec}}{\gamma} (1 + \frac{\eta P_{elec}}{\gamma})$$
$$\simeq \frac{\eta P_{elec}}{\gamma} + \left(\frac{\eta P_{elec}}{\gamma}\right)^2.$$
(S.18)

Therefore, we now have the dependence of the emission power on the electrical power, namely

$$P^{emission} \simeq N_{pol} \gamma_{rad}^{avg} \hbar \omega_{pola}^{avg} \left[\frac{\eta P_{elec}}{\gamma} + \left(\frac{\eta P_{elec}}{\gamma} \right)^2 \right] = a_1 P_{elec} + a_2 P_{elec}^2,$$
(S.19)

where $a_2/a_1 = \gamma/\eta$. We can therefore have access to the polariton population by fitting the curve corresponding to the measured emitted power versus the electrical injected power, as shown in the figure 4 in the main text. For the considered sample, the polariton population would reach more than one for an electrical injected power of 1.5 W (obtained for an electric field of 1 kV/cm).

From the two scenarios developed above, we can conclude that the polariton occupation from the most populated mode in our system is bound as follows:

$$2 \cdot 10^{-2} \le N_{pol} \le \simeq 1$$
. (S.20)

Emission / transmission comparison

The figure S.7 shows an emission spectrum on top of reflectivity one, for the same sample and magnetic field value. It highlights the fact that the emission maximum is aligned with the upper branch of the Landau polariton and that the lower branch remains invisible in emission.

Gate voltage effect

The figure S.8 displays two raw emission spectra obtained for two extremes gate bias value of +100 and -100 V and for the same magnetic field value. It highlights the specificity of Dirac materials which is a densitydependent mass inducing a shift of the CR energy and therefore a shift of the Landau polariton anti-crossing.

Amplitude and FWHM extraction

To extract the amplitude and the FWHM of the different emission peaks, we used a double-Gaussian fit for every injection bias value. The figure S.9 shows the 13 fits obtained on the experimental spectra.



FIG. S.7. Comparison of emission and transmission spectra at 0.75 T for sample A. (Top) Emission spectrum measured at a magnetic field of 0.75 T. (Bottom) Corresponding transmission spectrum obtained under the same conditions. The data clearly reveal that only the upper branch of the Landau polariton exhibits significant emission, highlighting the asymmetric population of polariton branches.



FIG. S.8. Gate voltage influence on Landau polariton emission. Emission spectra recorded at a magnetic field of 0.8 T for sample B, with a gate bias of -100 V (purple curve) and +100 V (blue curve). As the bias shifts from -100 V to +100 V, the upper branch of the Landau polariton undergoes a redshift of nearly 1 meV, attributed to the increase in cyclotron mass with higher electron density.



FIG. S.9. **Bias-dependent emission spectra at 0.9 T for sample A.** Emission spectra recorded for different injected bias values. The total double-Gaussian fit is overlaid (red dashed line), along with the individual Gaussian components corresponding to the UP1 (blue dotted line) and UP2 (red dotted line) polariton branches.